

## FDD5670

## 60V N-Channel PowerTrench® MOSFET

## **General Description**

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $R_{\text{DS}(\text{ON})}$  and fast switching speed. extremely low  $R_{\text{DS}(\text{ON})}$  in a small package.

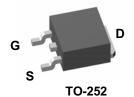
## **Applications**

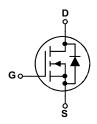
- DC/DC converter
- Motor drives

### **Features**

• 52 A, 60 V  $R_{DS(ON)} = 15 \text{ m}\Omega$  @  $V_{GS} = 10 \text{ V}$   $R_{DS(ON)} = 18 \text{ m}\Omega$  @  $V_{GS} = 6 \text{ V}$ 

- · Low gate charge
- Fast switching
- High performance trench technology for extremely low R<sub>DS(ON)</sub>





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		60	V
V <sub>GSS</sub>	Gate-Source Voltage		±20	V
I <sub>D</sub>	Drain Current - Continuous	(Note 3)	52	А
	– Pulsed	(Note 1a)	150	
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1)	83	W
		(Note 1a)	3.8	
		(Note 1b)	1.6	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +175	°C

## **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	1.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	40	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1b)	96	°C/W

**Package Marking and Ordering Information** 

Device Marking	Device	Reel Size	Tape width	Quantity
FDD5670 FDD5670		13"	16mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-Sc	ource Avalanche Ratings (Note	e 2)		•		
W <sub>DSS</sub>	Drain-Source Avalanche Energy	Single Pulse, V <sub>DD</sub> = 20 V, I <sub>D</sub> = 10A			360	mJ
I <sub>AR</sub>	Drain-Source Avalanche Current				10	Α
Off Char	acteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	60			V
ΔBV <sub>DSS</sub> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		53		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			1	μΑ
I <sub>GSSF</sub>	Gate–Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V},  V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	2.5	4	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		-6		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$V_{GS} = 10 \text{ V},  I_D = 10 \text{ A}$ $V_{GS} = 6 \text{ V},  I_D = 9 \text{ A}$ $V_{GS} = 10 \text{ V},  I_D = 10 \text{ A},  T_1 = 125^{\circ}\text{C}$		12 14 19	15 18 26	mΩ
I <sub>D(on)</sub>	On–State Drain Current	$V_{GS} = 10 \text{ V},  I_D = 10 \text{ A},  T_J = 125^{\circ}\text{C}$ $V_{GS} = 10 \text{ V}, \qquad V_{DS} = 5 \text{ V}$	60			Α
<b>g</b> FS	Forward Transconductance	$V_{DS} = 5 \text{ V}, \qquad I_{D} = 10 \text{ A}$		27		S
Dynamic	Characteristics		•		•	
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 15 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		2739		pF
Coss	Output Capacitance	f = 1.0 MHz		441		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			182		pF
Switchin	g Characteristics (Note 2)		•	•	•	•
t <sub>d(on)</sub>	Turn–On Delay Time	$V_{DD} = 30 \text{ V}, \qquad I_{D} = 1 \text{ A},$		20	32	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		12	24	ns
$t_{d(off)}$	Turn-Off Delay Time			60	95	ns
t <sub>f</sub>	Turn–Off Fall Time	1		24	38	ns
Qg	Total Gate Charge	$V_{DS} = 15 \text{ V}, \qquad I_{D} = 10 \text{ A},$		52	73	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		10		nC
$Q_{gd}$	Gate-Drain Charge	7		13		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 3.5 A (Note 2)		0.74	1.2	V

### Notes

 R<sub>8JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>8JC</sub> is guaranteed by design while R<sub>8CA</sub> is determined by the user's board design.



- a)  $R_{\theta JA} = 40^{\circ} \text{C/W}$  when mounted on a  $1 \text{in}^2$  pad of 2 oz copper
- b)  $R_{\theta JA} = 96^{\circ}CW$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

- **2.** Pulse Test: Pulse Width <  $300\mu$ s, Duty Cycle < 2.0%
- 3. Maximum current is calculated as:  $\sqrt{\frac{P_D}{R_{DS(ON)}}}$ where  $P_D$  is maximum power dissipation at  $T_C$  = 25°C and  $R_{DS(on)}$  is at  $T_{J(max)}$  and  $V_{GS}$  = 10V. Package current limitation is 21A

## **Typical Characteristics**

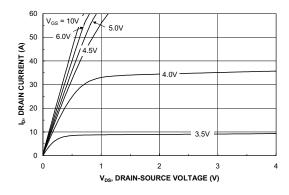


Figure 1. On-Region Characteristics.

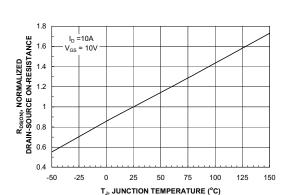


Figure 3. On-Resistance Variation withTemperature.

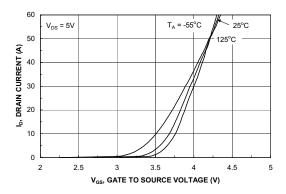


Figure 5. Transfer Characteristics.

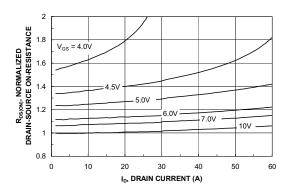


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

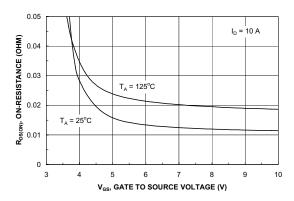


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

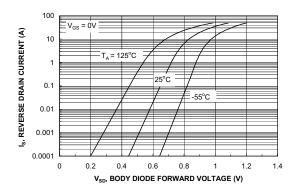
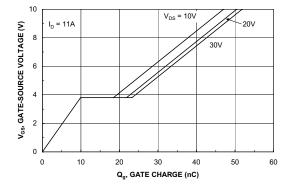


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## **Typical Characteristics**



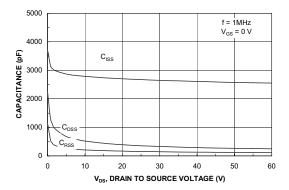
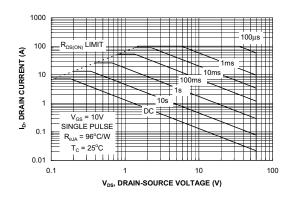


Figure 7. Gate Charge Characteristics.





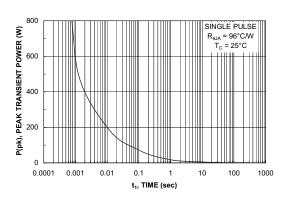


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

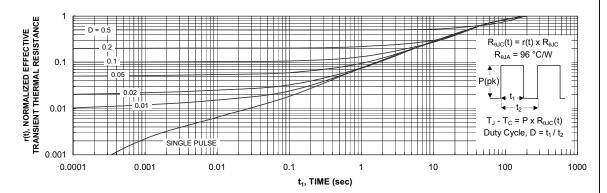


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.







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